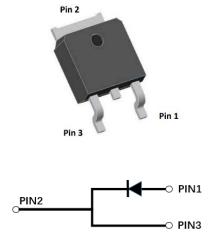
Silicon Carbide Schottky Diode

V _{RRM}	1200V
I _{F (135°C)}	3.7A
Qc	13.7nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- Package: TO-252 Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free
- Terminals: Tin plated leads
- Polarity: As marked

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112002DG1
Reverse voltage (Repetitive peak) @ T _j =25°C	V _{RRM}	V	1200
Reverse voltage (Surge peak) @ Tj=25°C	V _{RSM}	V	1200
Reverse voltage (DC) @ Tj=25°C	V _{DC}	V	1200
Continuous forward current @ $T_c=25^{\circ}C$			7.6
Continuous forward current @ T _c =135°C	I _F	А	3.7
Continuous forward current @ T _c =160°C			2
Non-repetitive peak forward surge current @ $T_c=25^{\circ}C$, tp=10ms, Half Sine Wave	I _{FSM}	А	29
Power Dissipation@ T _c =25°C	_	W	40
Power Dissipation@ T _c =110°C	Ртот		17
i²t Value@ T _c =25°C ,tp=10ms	∫ i²dt	A ² S	4.2
Operating junction and Storage temperature range	T _j ,T _{stg}	°C	-55 to +175

■Maximum Ratings (T_c=25°C Unless otherwise specified)

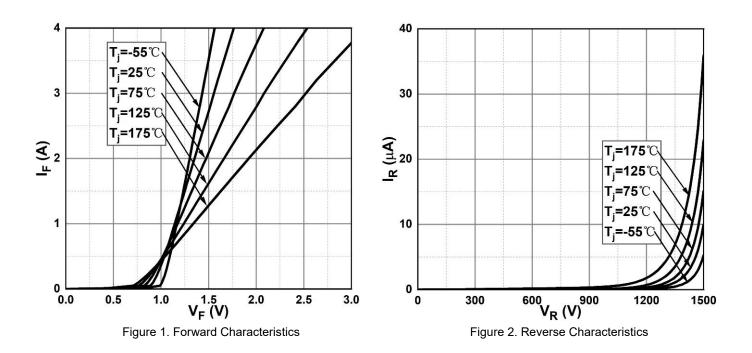
Electrical Characteristics

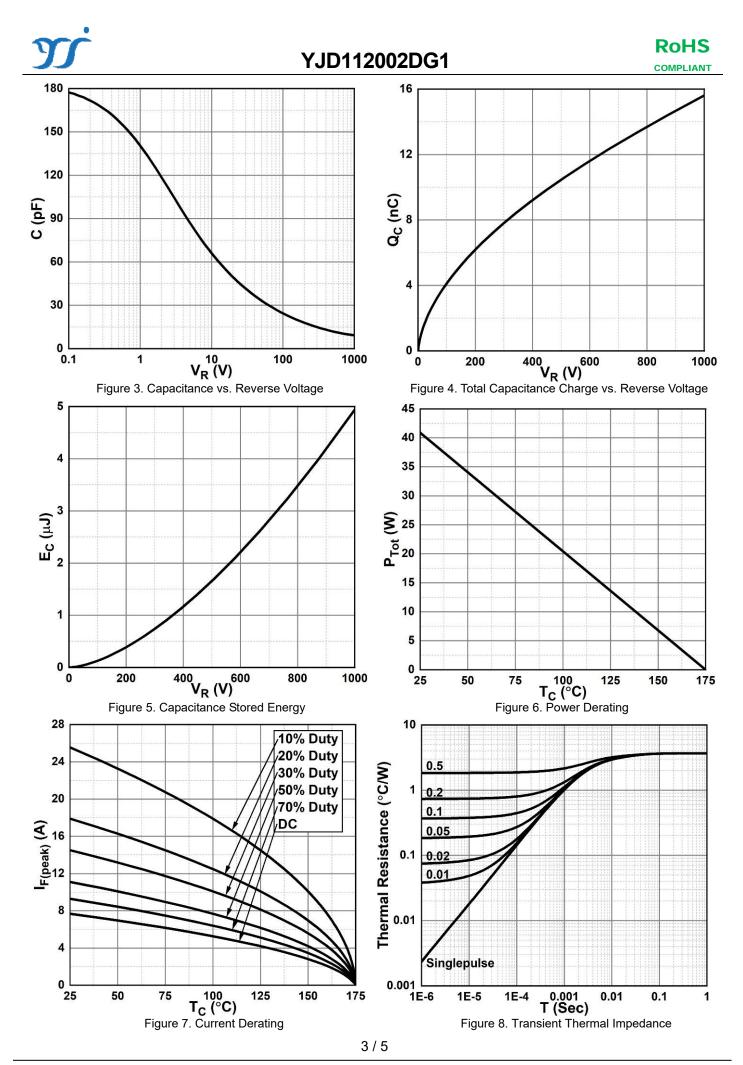
PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V _F	V	I _F =2A, T _j =25°C	1.36	1.55
			I _F =2A, T _j =175°C	2.0	-
Reverse leakage current	I _R	μΑ	V _R =1200V, T _j =25°C	0.5	10
			V _R =1200V, T _j =175°C	10	-
Total capacitive charge	Qc	nC	$V_{\text{R}}\text{=}800\text{V},T_{j}\text{=}25^{\circ}\text{C}$, $Q_{\text{C}}\text{=}\text{J}_{0}^{\ \text{VR}}\text{C}(\text{V})\text{dV}$	13.7	-
Total capacitance	С	pF	V _R =0V, f=1MHZ	183	-
			V _R =400V, f=1MHZ	13	-
			V _R =800V, f=1MHZ	10	-
Capacitance Stored Energy	Ec	μJ	V _R =800V	3.5	-

Thermal Characteristics $(T_a=25^{\circ}C \text{ Unless otherwise specified})$

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{_{ ext{ hetaJ-C}}}$	°C /W	3.67

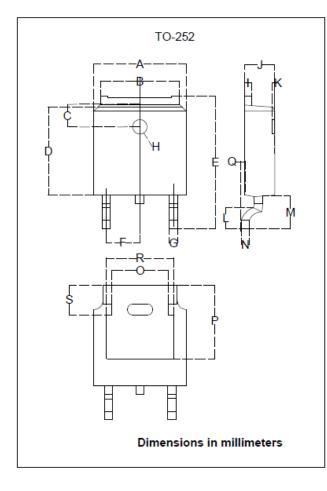
■Typical Characteristics







Outline Dimensions



TO-252			
Dim	Min	Max	
А	6.500	6.700	
В	5.100	5.460	
С	1.400	1.800	
D	6.000	6.200	
Е	10.000	10.400	
F	2.166	2.366	
G	0.660	0.860	
Н	Ф1.050	Ф1.350	
I	0.460	0.580	
J	2.200	2.400	
К	0	0.300	
L	0.890	2.290	
М	2.730	3.080	
Ν	0.430	0.580	
0	4.20	4.95	
Р	5.15	5.45	
Q	0	0.2	
R	4.50	5.10	
S	1.60	2.40	



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